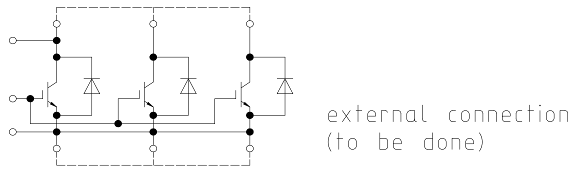
FZ2400R17HE4P_B9

IHM-B 模块 采用第四代高速沟槽栅/场终止IGBT和第四代发射极控制二极管 和预涂导热介质
IHM-B module with fast Trench/Fieldstop IGBT4 and Emitter Controlled diode and pre-applied Thermal Interface Material



V_{CES} = 1700V
$I_{C\ nom}$ = 2400A / I_{CRM} = 4800A

典型应用
- 大功率变流器
- 电机传动

Typical Applications
- High power converters
- Motor drives

电气特性
- 提高工作结温 $T_{vj\ op}$
- 低开关损耗
- 低 V_{CEsat}
- $T_{vj\ op}$ = 150°C

Electrical Features
- Extended operating temperature $T_{vj\ op}$
- Low switching losses
- Low V_{CEsat}
- $T_{vj\ op}$ = 150°C

机械特性
- 4 kV 交流 1分钟 绝缘
- 封装的 CTI > 400
- 高爬电距离和电气间隙
- 高功率密度
- IHM B 封装
- 铜基板
- 符合RoHS
- 预涂导热介质

Mechanical Features
- 4 kV AC 1min insulation
- Package with CTI > 400
- High creepage and clearance distances
- High power density
- IHM B housing
- Copper base plate
- RoHS compliant
- Pre-applied Thermal Interface Material

Module Label Code

Barcode Code 128

Sample
00000123456000000000000

DMX - Code

Content of the Code	**Digit**
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT,Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1700	V
连续集电极直流电流 Continuous DC collector current	T_H = 80°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$	2400	A
集电极重复峰值电流 Repetitive peak collector current	t_P = 1 ms	I_{CRM}	4800	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

				min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	I_C = 2400 A, V_{GE} = 15 V I_C = 2400 A, V_{GE} = 15 V I_C = 2400 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE\,sat}$		1,95 2,35 2,45	2,30 2,75 2,90	V V V
栅极阈值电压 Gate threshold voltage	I_C = 96,0 mA, V_{CE} = V_{GE}, T_{vj} = 25°C		V_{GEth}	5,20	5,80	6,40	V
栅极电荷 Gate charge	V_{GE} = -15 V ... +15 V		Q_G		25,0		µC
内部栅极电阻 Internal gate resistor	T_{vj} = 25°C		R_{Gint}		0,65		Ω
输入电容 Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		195		nF
反向传输电容 Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{res}		6,30		nF
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE} = 1700 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	I_C = 2400 A, V_{CE} = 900 V V_{GE} = ±15 V R_{Gon} = 0,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,on}$		0,46 0,50 0,53		µs µs µs
上升时间(电感负载) Rise time, inductive load	I_C = 2400 A, V_{CE} = 900 V V_{GE} = ±15 V R_{Gon} = 0,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0,21 0,22 0,23		µs µs µs
关断延迟时间(电感负载) Turn-off delay time, inductive load	I_C = 2400 A, V_{CE} = 900 V V_{GE} = ±15 V R_{Goff} = 0,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,off}$		1,40 1,55 1,60		µs µs µs
下降时间(电感负载) Fall time, inductive load	I_C = 2400 A, V_{CE} = 900 V V_{GE} = ±15 V R_{Goff} = 0,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0,16 0,41 0,50		µs µs µs
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	I_C = 2400 A, V_{CE} = 900 V, L_S = 50 nH V_{GE} = ±15 V, di/dt = 11500 A/µs (T_{vj} = 150°C) R_{Gon} = 0,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		510 620 650		mJ mJ mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	I_C = 2400 A, V_{CE} = 900 V, L_S = 50 nH V_{GE} = ±15 V, du/dt = 2500 V/µs (T_{vj} = 150°C) R_{Goff} = 0,8 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		630 920 1000		mJ mJ mJ
短路数据 SC data	V_{GE} ≤ 15 V, V_{CC} = 1000 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt	t_P ≤ 10 µs, T_{vj} = 150°C	I_{SC}		11000		A
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个 IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}			13,1	K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

二极管,逆变器 / Diode, Inverter

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1700	V
连续正向直流电流 Continuous DC forward current		I_F	2400	A
正向重复峰值电流 Repetitive peak forward current	t_P = 1 ms	I_{FRM}	4800	A
I2t-值 I²t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I^2t	1000 940	kA²s kA²s

特征值 / Characteristic Values

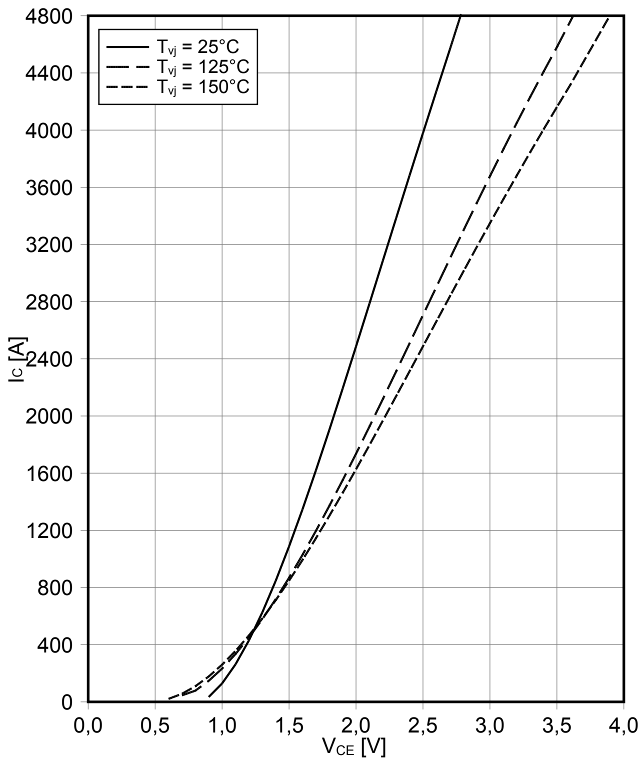
				min.	typ.	max.	
正向电压 Forward voltage	I_F = 2400 A, V_{GE} = 0 V I_F = 2400 A, V_{GE} = 0 V I_F = 2400 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,80 1,90 1,95	2,20 2,30 2,40	V V V
反向恢复峰值电流 Peak reverse recovery current	I_F = 2400 A, - di_F/dt = 11500 A/µs (T_{vj}=150°C) V_R = 900 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		1950 2450 2600		A A A
恢复电荷 Recovered charge	I_F = 2400 A, - di_F/dt = 11500 A/µs (T_{vj}=150°C) V_R = 900 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		530 960 1100		µC µC µC
反向恢复损耗（每脉冲） Reverse recovery energy	I_F = 2400 A, - di_F/dt = 11500 A/µs (T_{vj}=150°C) V_R = 900 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		330 660 790		mJ mJ mJ
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material		R_{thJH}			20,2	K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40		150	°C

模块 / Module

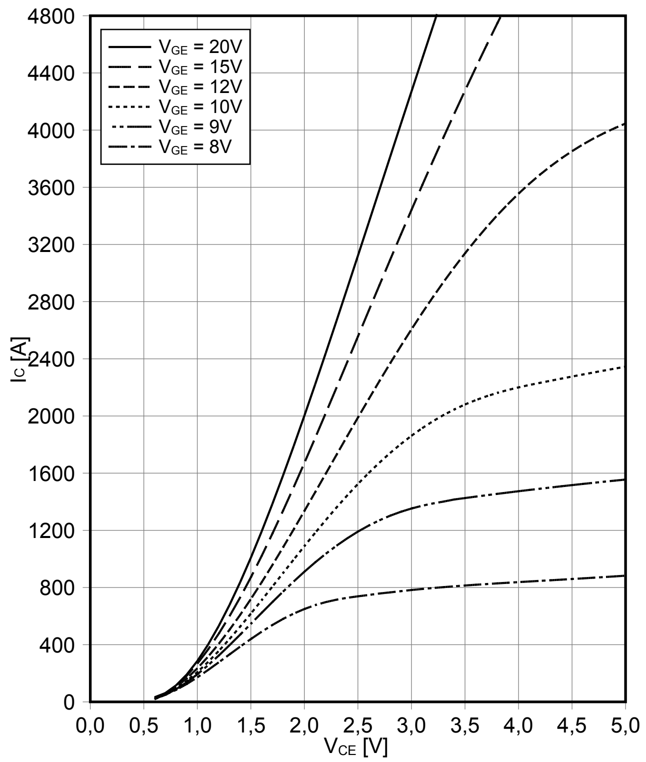
绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}		4,0		kV
模块基板材料 Material of module baseplate				Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)			Al_2O_3		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal			32,2 32,2		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal			19,1 19,1		mm
相对电痕指数 Comperative tracking index		CTI		> 400		
			min.	typ.	max.	
杂散电感,模块 Stray inductance module		L_{sCE}		6,0		nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T_H = 25°C, 每个开关 / per switch	$R_{CC'+EE'}$		0,10		mΩ
储存温度 Storage temperature		T_{stg}	-40		125	°C
最高基板工作温度 Maximum baseplate operation temperature		T_{BPmax}			125	°C
模块安装的安装扭距 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	4,25		5,75	Nm
端子联接扭距 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note 螺丝 M8 根据相应的应用手册进行安装 Screw M8 - Mounting according to valid application note	M	1,8 8,0	- -	2,1 10	Nm Nm
重量 Weight		G		1900		g

Lagerung und Transport von Modulen mit TIM laut AN2012-07
Storage and shipment of modules with TIM according to AN2012-07

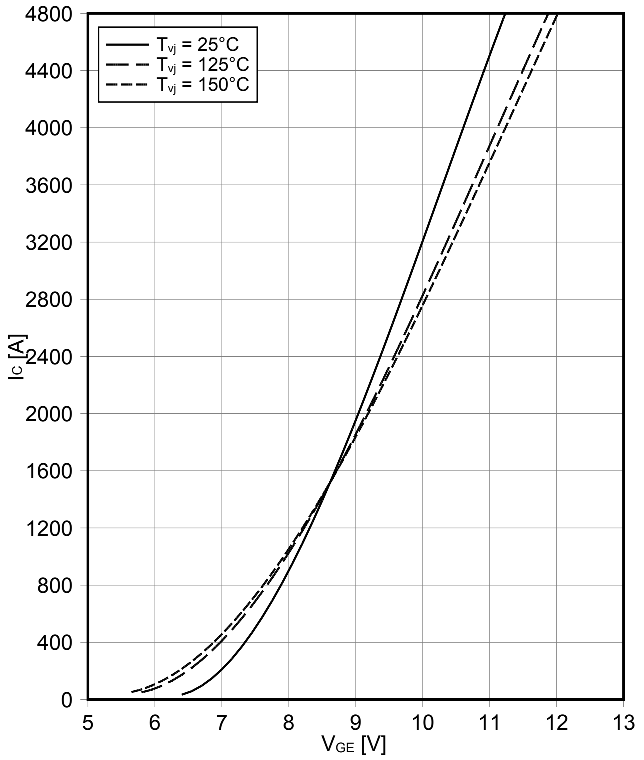
输出特性 IGBT, 逆变器 （典型)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V



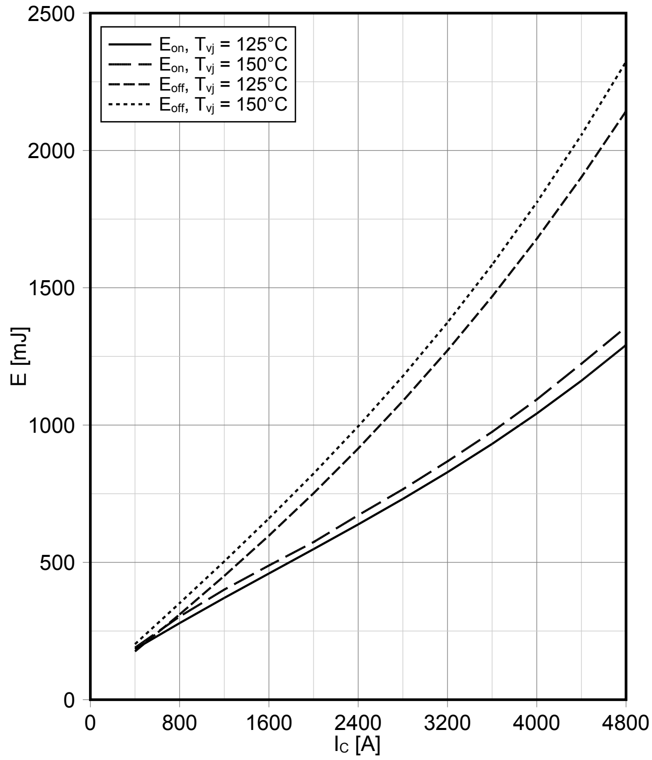
输出特性 IGBT, 逆变器 （典型)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150$°C



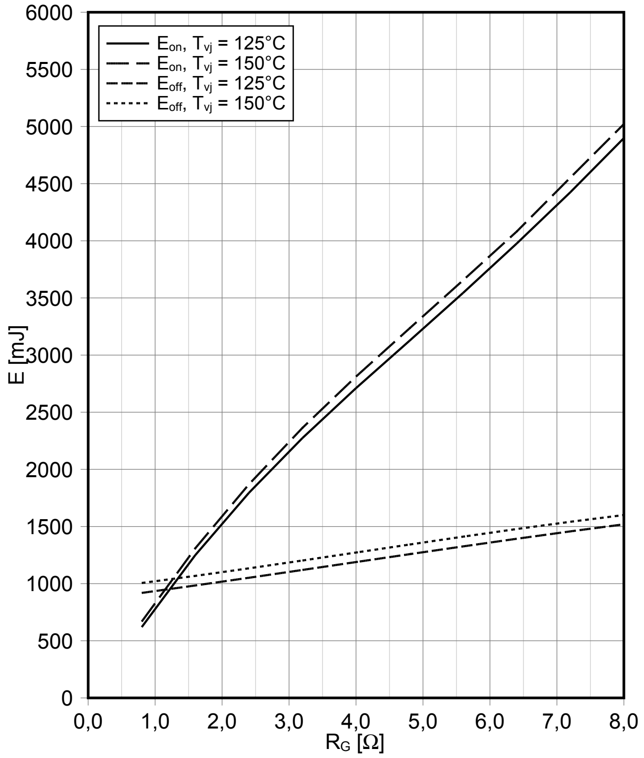
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT,Inverter (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



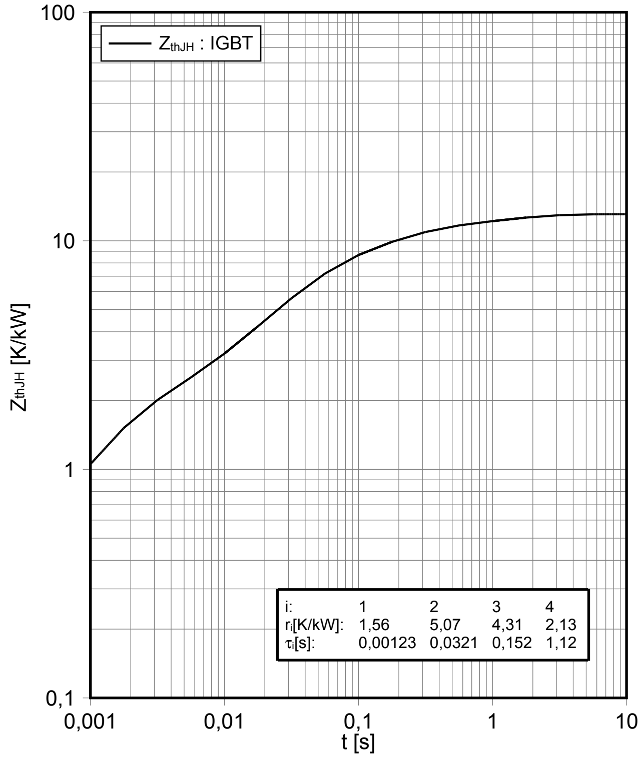
开关损耗 IGBT, 逆变器 （典型)
switching losses IGBT,Inverter (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$V_{GE} = \pm 15$ V, $R_{Gon} = 0.8\ \Omega$, $R_{Goff} = 0.8\ \Omega$, $V_{CE} = 900$ V



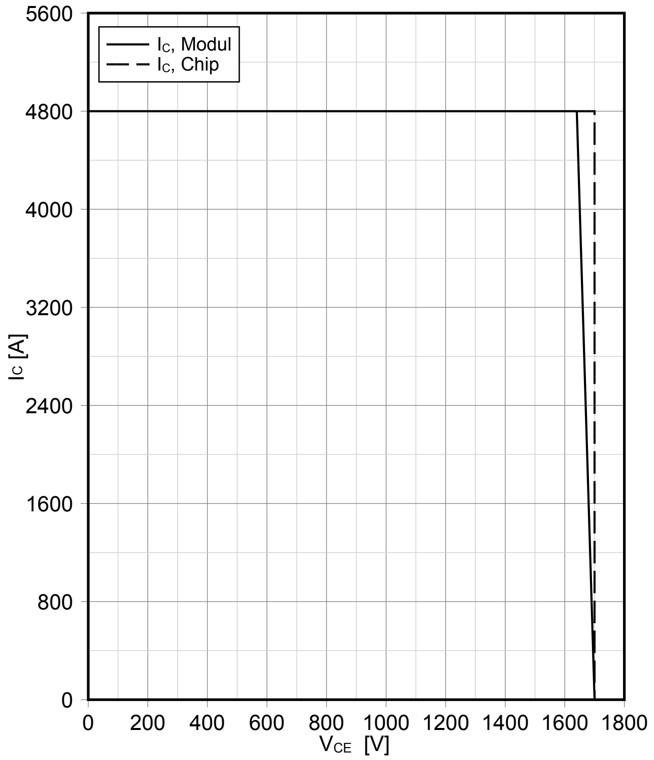
开关损耗 IGBT, 逆变器 （典型)
switching losses IGBT,Inverter (typical)
E_{on} = f (R_G), E_{off} = f (R_G)
V_{GE} = ±15 V, I_C = 2400 A, V_{CE} = 900 V



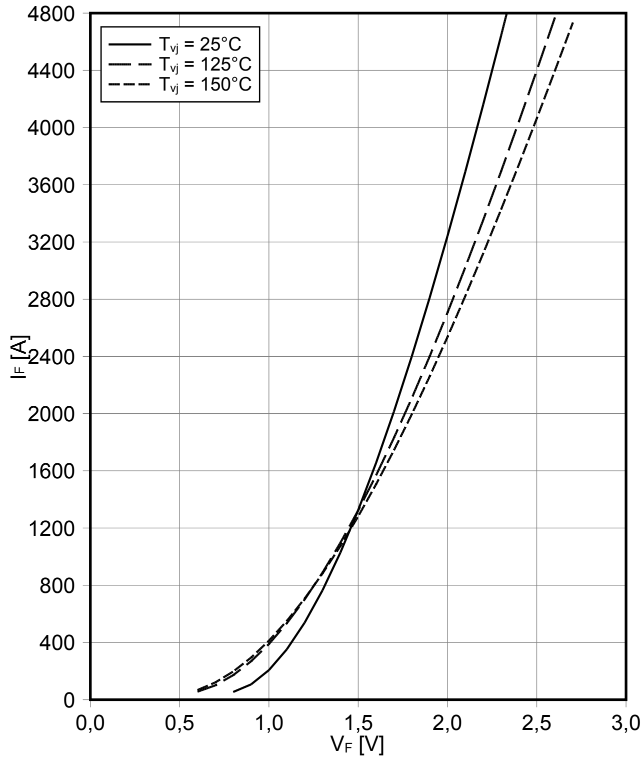
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT,Inverter
Z_{thJH} = f (t)



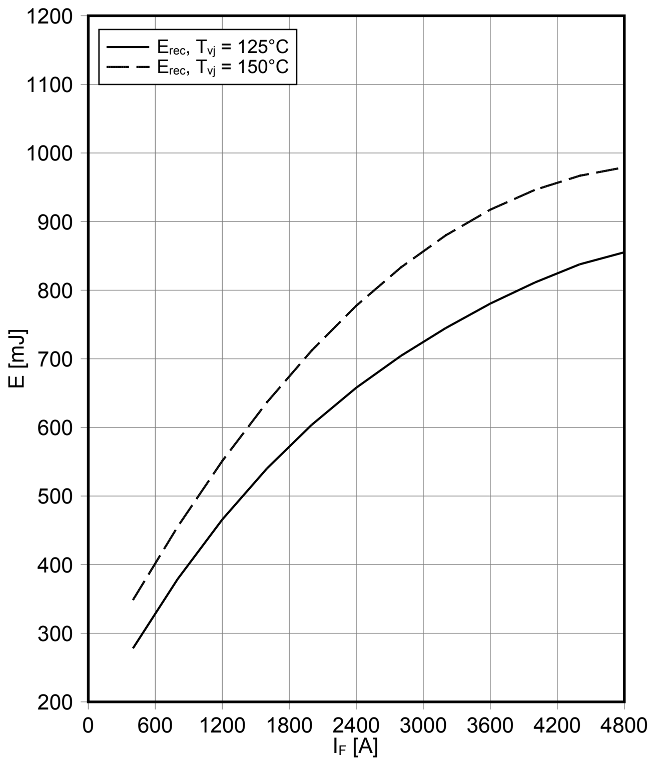
反偏安全工作区 IGBT, 逆变器 （RBSOA）
reverse bias safe operating area IGBT,Inverter (RBSOA)
I_C = f (V_{CE})
V_{GE} = ±15 V, R_{Goff} = 0.8 Ω, T_{vj} = 150°C



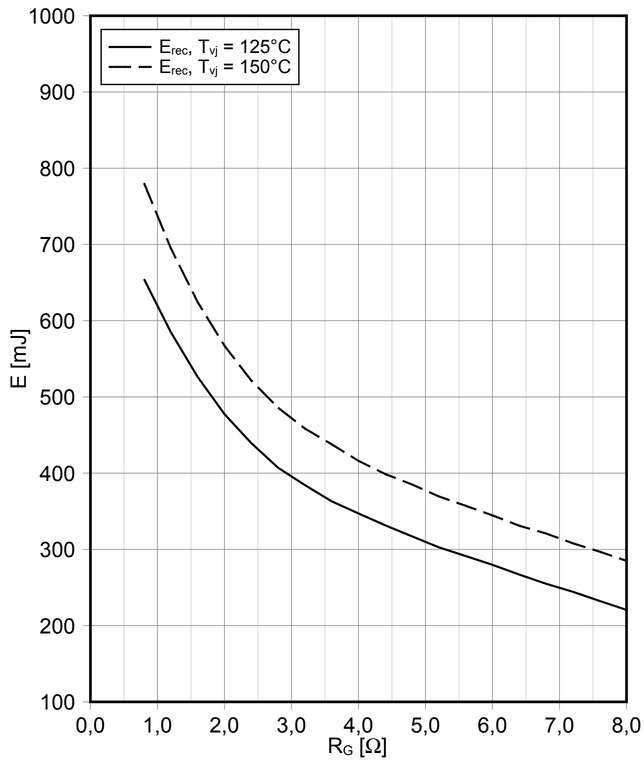
正向偏压特性 二极管,逆变器 （典型)
forward characteristic of Diode, Inverter (typical)
I_F = f (V_F)



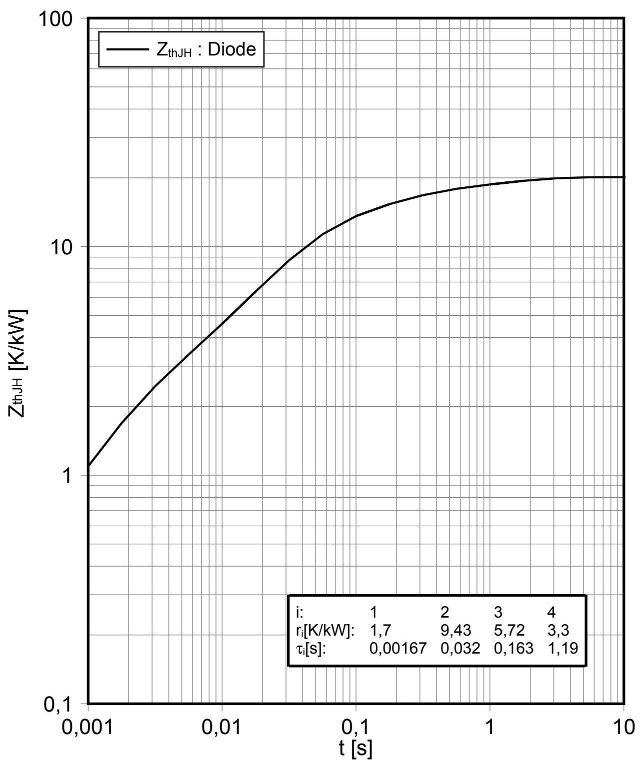
开关损耗 二极管,逆变器 （典型)
switching losses Diode, Inverter (typical)
$E_{rec} = f\ (I_F)$
$R_{Gon} = 0.8\ \Omega$, $V_{CE} = 900\ V$



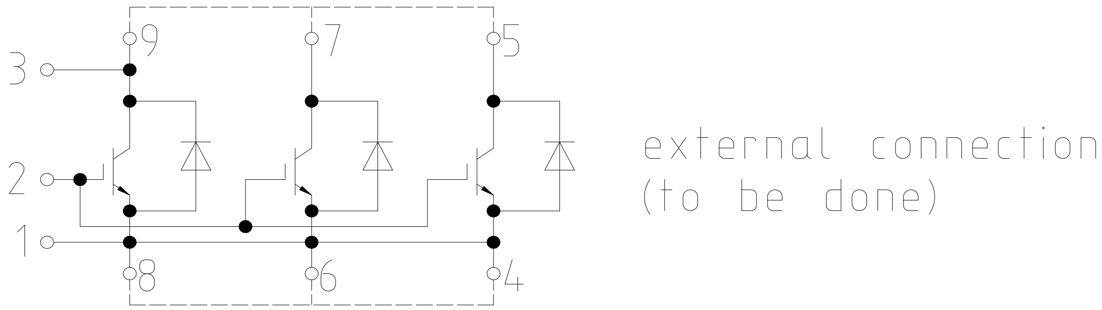
开关损耗 二极管,逆变器 （典型)
switching losses Diode, Inverter (typical)
$E_{rec} = f\ (R_G)$
$I_F = 2400\ A$, $V_{CE} = 900\ V$



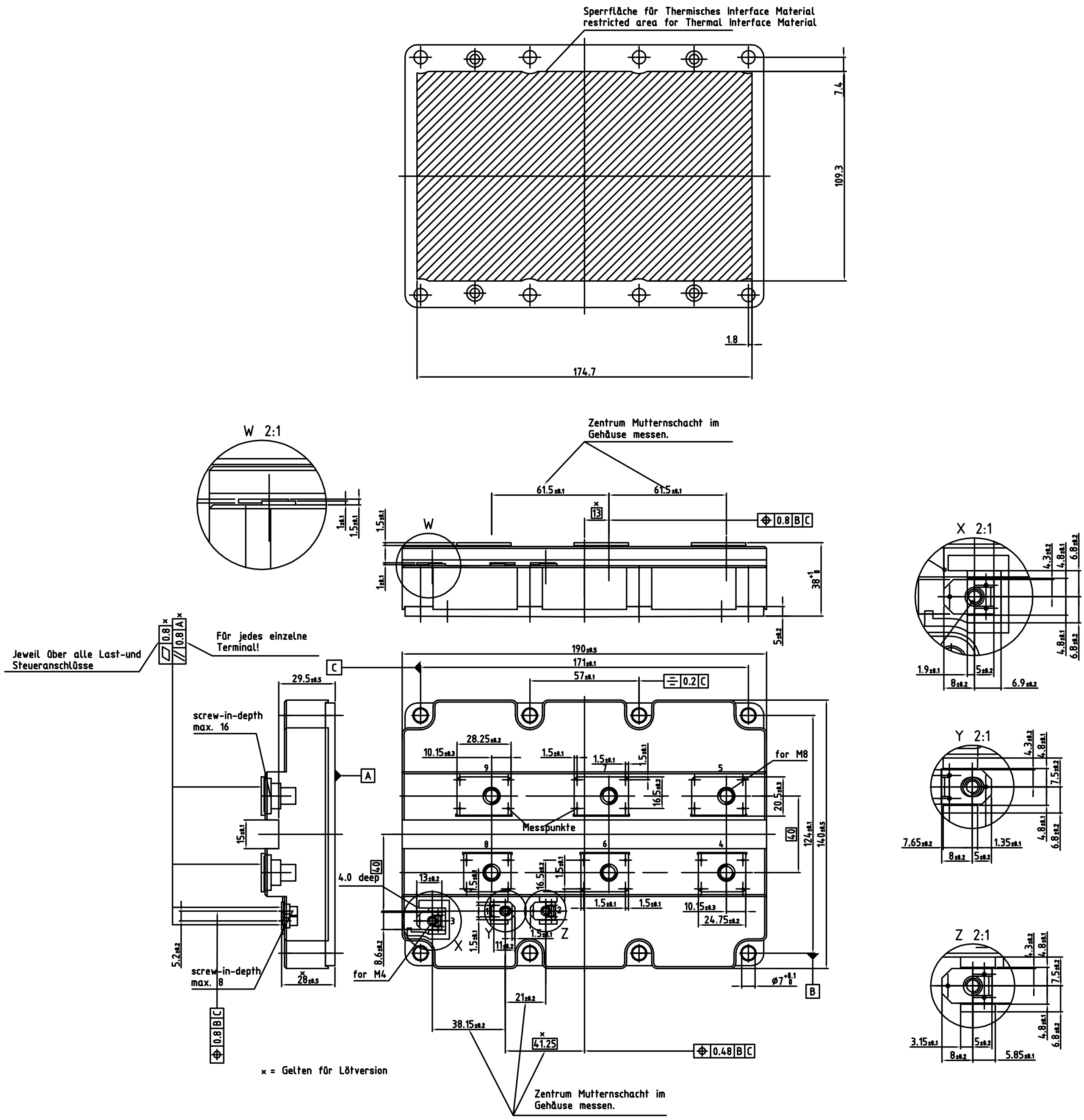
瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter
$Z_{thJH} = f\ (t)$



接线图 / Circuit diagram



封装尺寸 / Package outlines



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Edition 2016-10-17

Published by
Infineon Technologies AG
81726 München, Germany

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